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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	77
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p030-1vqg100i

I/Os Per Package ¹

ProASIC3 Devices	A3P015 ²	A3P030	A3P060	A3P125	A3P250 ³		A3P400 ³		A3P600		A3P1000	
Cortex-M1 Devices					M1A3P250 ^{3,5}		M1A3P400 ³		M1A3P600		M1A3P1000	
Package	I/O Type											
	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O	Single-Ended I/O ⁴	Differential I/O Pairs	Single-Ended I/O ⁴	Differential I/O Pairs	Single-Ended I/O ⁴	Differential I/O Pairs	Single-Ended I/O ⁴	Differential I/O Pairs
QN48	–	34	–	–	–	–		–	–	–	–	–
QN68	49	49	–	–	–	–	–	–		–	–	–
QN132 ⁷	–	81	80	84	87	19	–	–		–	–	–
CS121	–	–	96	–	–	–	–	–	–	–	–	–
VQ100	–	77	71	71	68	13	–	–		–	–	–
TQ144	–	–	91	100	–	–	–	–	–	–	–	–
PQ208	–	–	–	133	151	34	151	34	154	35	154	35
FG144	–	–	96	97	97	24	97	25	97	25	97	25
FG256 ^{5,6}	–	–	–	–	157	38	178	38	177	43	177	44
FG484 ⁶	–	–	–	–	–	–	194	38	235	60	300	74

Notes:

1. When considering migrating your design to a lower- or higher-density device, refer to the [ProASIC3 FPGA Fabric User Guide](#) to ensure complying with design and board migration requirements.
2. A3P015 is not recommended for new designs.
3. For A3P250 and A3P400 devices, the maximum number of LVPECL pairs in east and west banks cannot exceed 15. Refer to the [ProASIC3 FPGA Fabric Users Guide](#) for position assignments of the 15 LVPECL pairs.
4. Each used differential I/O pair reduces the number of single-ended I/Os available by two.
5. The M1A3P250 device does not support FG256 package.
6. FG256 and FG484 are footprint-compatible packages.
7. Package not available.

Table 1 • ProASIC3 FPGAs Package Sizes Dimensions

Package	CS121	QN48	QN68	QN132 *	VQ100	TQ144	PQ208	FG144	FG256	FG484
Length × Width (mm × mm)	6 × 6	6 × 6	8 × 8	8 × 8	14 × 14	20 × 20	28 × 28	13 × 13	17 × 17	23 × 23
Nominal Area (mm ²)	36	36	64	64	196	400	784	169	289	529
Pitch (mm)	0.5	0.4	0.4	0.5	0.5	0.5	0.5	1.0	1.0	1.0
Height (mm)	0.99	0.90	0.90	0.75	1.00	1.40	3.40	1.45	1.60	2.23

Note: * Package not available

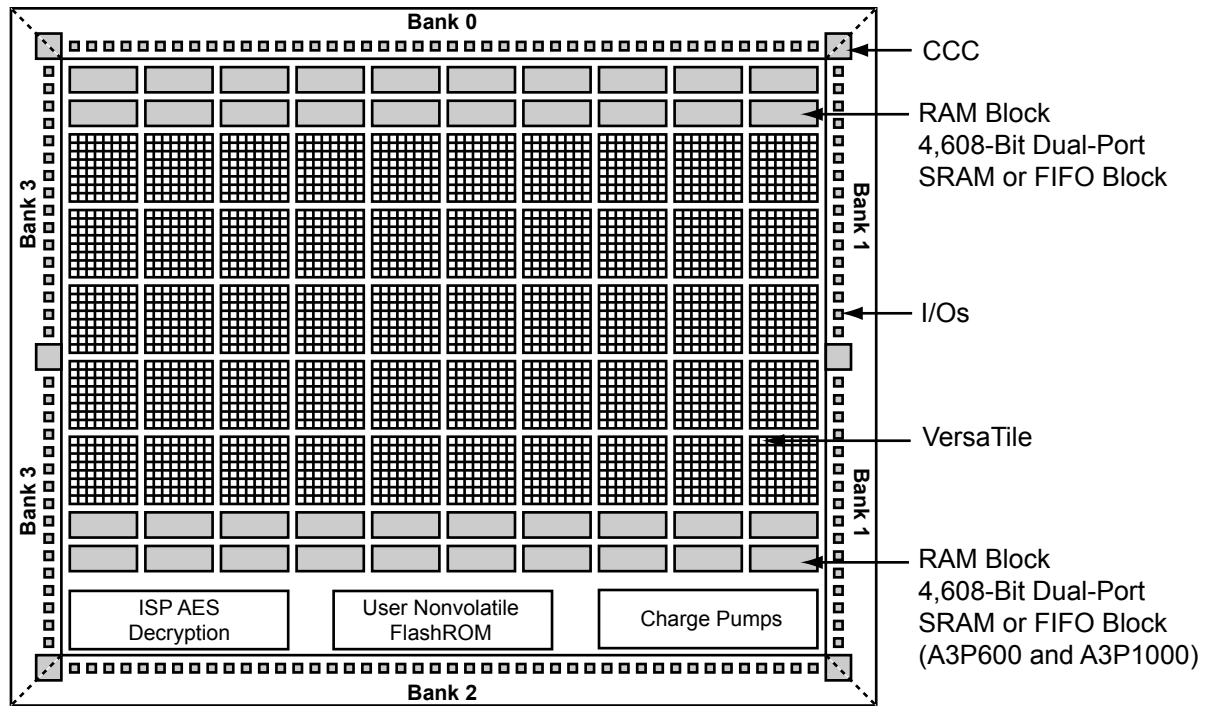


Figure 1-2 • ProASIC3 Device Architecture Overview with Four I/O Banks (A3P250, A3P600, and A3P1000)

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the ProASIC3 core tile as either a three-input lookup table (LUT) equivalent or as a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the Microsemi ProASIC family of third-generation architecture flash FPGAs. VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.

VersaTiles

The ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS}® core tiles. The ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.

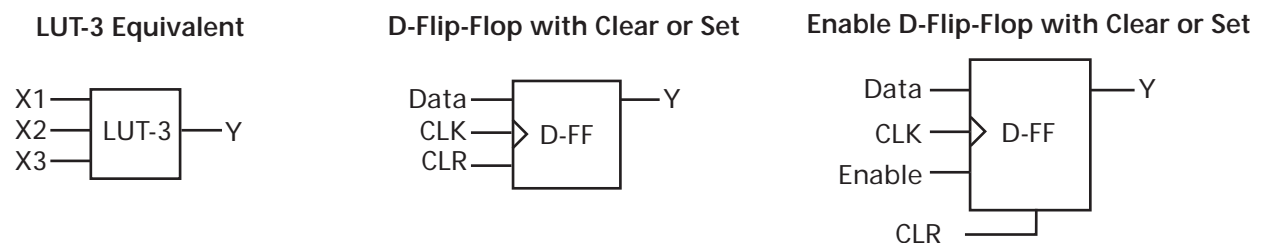


Figure 1-3 • VersaTile Configurations

2 – ProASIC3 DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in [Table 2-1](#) may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in [Table 2-2 on page 2-2](#) is not implied.

Table 2-1 • Absolute Maximum Ratings

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	V
VMV	DC I/O input buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T _{STG} ²	Storage temperature	–65 to +150	°C
T _J ²	Junction temperature	+125	°C

Notes:

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in [Table 2-4 on page 2-3](#).
2. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on [page 3-1](#) for further information.
3. For flash programming and retention maximum limits, refer to [Table 2-3 on page 2-3](#), and for recommended operating limits, refer to [Table 2-2 on page 2-2](#).

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-2 on page 2-5](#).

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-2 on page 2-5](#)).
2. $VCCI > VCC - 0.75 \text{ V}$ (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: $0.6 \text{ V} < \text{trip_point_up} < 1.2 \text{ V}$

Ramping down: $0.5 \text{ V} < \text{trip_point_down} < 1.1 \text{ V}$

VCC Trip Point:

Ramping up: $0.6 \text{ V} < \text{trip_point_up} < 1.1 \text{ V}$

Ramping down: $0.5 \text{ V} < \text{trip_point_down} < 1 \text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see [Figure 2-2 on page 2-5](#) for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75 \text{ V} \pm 0.25 \text{ V}$), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the [ProASIC3 FPGA Fabric User's Guide](#) for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in [Table 2-5 on page 2-6](#).

P = Power dissipation

The absolute maximum junction temperature is 100°C. EQ 1 shows a sample calculation of the absolute maximum power dissipation allowed for a 484-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja} (\text{°C/W})} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{20.5^{\circ}\text{C/W}} = 1.463 \text{ W}$$

EQ 1

Table 2-5 • Package Thermal Resistivities

Package Type	Device	Pin Count	θ_{jc}	θ_{ja}			Units
				Still Air	200 ft/min	500 ft/min	
Quad Flat No Lead	A3P030	132	0.4	21.4	16.8	15.3	°C/W
	A3P060	132	0.3	21.2	16.6	15.0	°C/W
	A3P125	132	0.2	21.1	16.5	14.9	°C/W
	A3P250	132	0.1	21.0	16.4	14.8	°C/W
Very Thin Quad Flat Pack (VQFP)	All devices	100	10.0	35.3	29.4	27.1	°C/W
Thin Quad Flat Pack (TQFP)	All devices	144	11.0	33.5	28.0	25.7	°C/W
Plastic Quad Flat Pack (PQFP)	All devices	208	8.0	26.1	22.5	20.8	°C/W
Fine Pitch Ball Grid Array (FBGA)	See note*	144	3.8	26.9	22.9	21.5	°C/W
	See note*	256	3.8	26.6	22.8	21.5	°C/W
	See note*	484	3.2	20.5	17.0	15.9	°C/W
	A3P1000	144	6.3	31.6	26.2	24.2	°C/W
	A3P1000	256	6.6	28.1	24.4	22.7	°C/W
	A3P1000	484	8.0	23.3	19.0	16.7	°C/W

Note: *This information applies to all ProASIC3 devices except the A3P1000. Detailed device/package thermal information will be available in future revisions of the datasheet.

Temperature and Voltage Derating Factors

Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays
 (normalized to $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425 \text{ V}$)

Array Voltage VCC (V)	Junction Temperature (°C)					
	–40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.88	0.93	0.95	1.00	1.02	1.04
1.500	0.83	0.88	0.90	0.95	0.96	0.98
1.575	0.80	0.84	0.87	0.91	0.93	0.94

RAM Contribution— P_{MEMORY}

$$P_{\text{MEMORY}} = P_{\text{AC11}} * N_{\text{BLOCKS}} * F_{\text{READ-CLOCK}} * \beta_2 + P_{\text{AC12}} * N_{\text{BLOCK}} * F_{\text{WRITE-CLOCK}} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{\text{READ-CLOCK}}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations.

$F_{\text{WRITE-CLOCK}}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in [Table 2-17 on page 2-14](#).

PLL Contribution— P_{PLL}

$$P_{\text{PLL}} = P_{\text{DC4}} + P_{\text{AC13}} * F_{\text{CLKOUT}}$$

F_{CLKOUT} is the output clock frequency.¹

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = (100% + 50% + 25% + 12.5% + ... + 0.78125%) / 8

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-16 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-17 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

1. The PLL dynamic contribution depends on the input clock frequency, the number of output clock signals generated by the PLL, and the frequency of each output clock. If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($P_{\text{AC14}} * F_{\text{CLKOUT}}$ product) to the total PLL contribution.

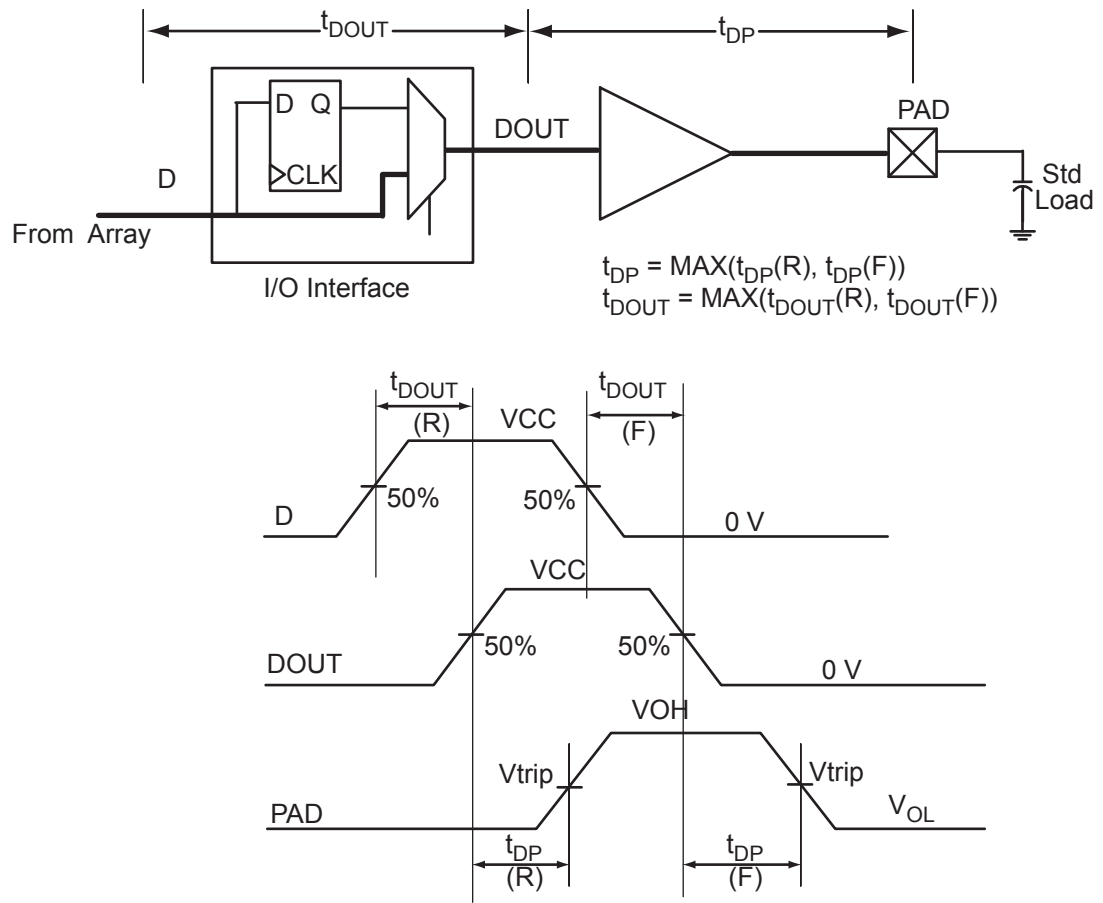


Figure 2-5 • Output Buffer Model and Delays (Example)

Table 2-29 • I/O Output Buffer Maximum Resistances¹
Applicable to Standard Plus I/O Banks

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range ⁴	100 μA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / IOL_{spec}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / IOH_{spec}$
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

Single-Ended I/O Characteristics

3.3 V LVTTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTTL input buffer and push-pull output buffer.

Table 2-37 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	10	10
24 mA	−0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-38 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

3.3 V LVTTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA ³	Max mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	10	10
4 mA	−0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	10	10
6 mA	−0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	10	10
8 mA	−0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	10	10
12 mA	−0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	10	10
16 mA	−0.3	0.8	2	3.6	0.4	2.4	16	16	109	103	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-61 • 2.5 V LVCMOS Low Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.60	11.40	0.04	1.31	0.43	11.22	11.40	2.68	2.20	13.45	13.63	ns
	–1	0.51	9.69	0.04	1.11	0.36	9.54	9.69	2.28	1.88	11.44	11.60	ns
	–2	0.45	8.51	0.03	0.98	0.32	8.38	8.51	2.00	1.65	10.05	10.18	ns
6 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
8 mA	Std.	0.60	7.96	0.04	1.31	0.43	8.11	7.81	3.05	2.89	10.34	10.05	ns
	–1	0.51	6.77	0.04	1.11	0.36	6.90	6.65	2.59	2.46	8.80	8.55	ns
	–2	0.45	5.94	0.03	0.98	0.32	6.05	5.84	2.28	2.16	7.72	7.50	ns
12 mA	Std.	0.60	6.18	0.04	1.31	0.43	6.29	5.92	3.30	3.32	8.53	8.15	ns
	–1	0.51	5.26	0.04	1.11	0.36	5.35	5.03	2.81	2.83	7.26	6.94	ns
	–2	0.45	4.61	0.03	0.98	0.32	4.70	4.42	2.47	2.48	6.37	6.09	ns
16 mA	Std.	0.60	5.76	0.04	1.31	0.43	5.87	5.53	3.36	3.44	8.11	7.76	ns
	–1	0.51	4.90	0.04	1.11	0.36	4.99	4.70	2.86	2.92	6.90	6.60	ns
	–2	0.45	4.30	0.03	0.98	0.32	4.38	4.13	2.51	2.57	6.05	5.80	ns
24 mA	Std.	0.60	5.51	0.04	1.31	0.43	5.50	5.51	3.43	3.87	7.74	7.74	ns
	–1	0.51	4.68	0.04	1.11	0.36	4.68	4.68	2.92	3.29	6.58	6.59	ns
	–2	0.45	4.11	0.03	0.98	0.32	4.11	4.11	2.56	2.89	5.78	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

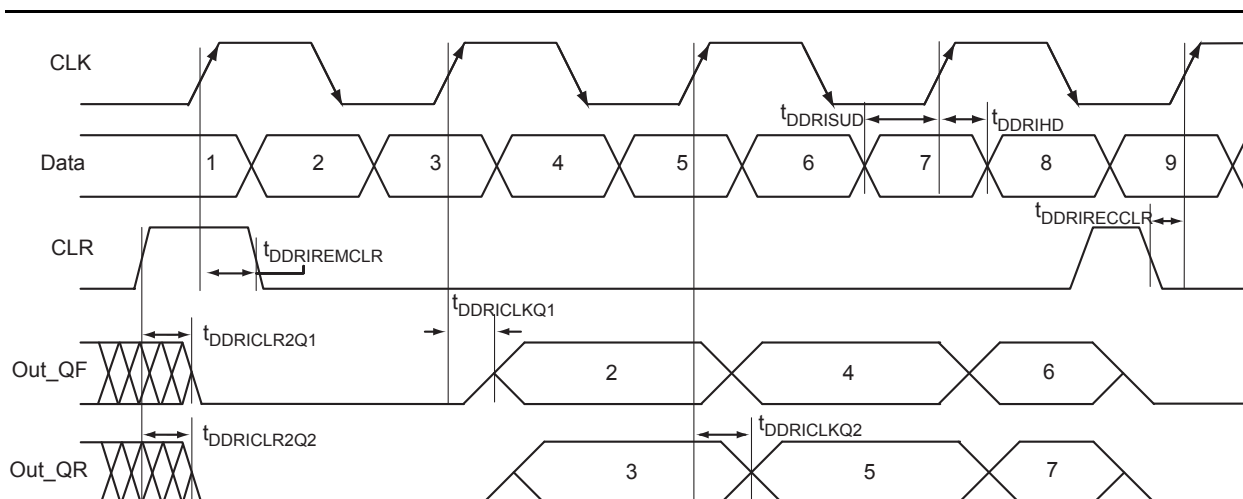


Figure 2-21 • Input DDR Timing Diagram

Timing Characteristics

Table 2-102 • Input DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DDRICKQ1}	Clock-to-Out Out_QR for Input DDR	0.27	0.31	0.37	ns
t_{DDRICKQ2}	Clock-to-Out Out_QF for Input DDR	0.39	0.44	0.52	ns
t_{DDRISUD}	Data Setup for Input DDR (Fall)	0.25	0.28	0.33	ns
	Data Setup for Input DDR (Rise)	0.25	0.28	0.33	ns
t_{DDRIMHD}	Data Hold for Input DDR (Fall)	0.00	0.00	0.00	ns
	Data Hold for Input DDR (Rise)	0.00	0.00	0.00	ns
$t_{\text{DDRIMCLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.46	0.53	0.62	ns
$t_{\text{DDRIMCLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.57	0.65	0.76	ns
t_{DDRIMCLR}	Asynchronous Clear Removal time for Input DDR	0.00	0.00	0.00	ns
$t_{\text{DDRIMRECCLR}}$	Asynchronous Clear Recovery time for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRIMWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
F_{DDRIMAX}	Maximum Frequency for Input DDR	350	309	263	MHz

Note: For specific junction temperature and voltage-supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

Table 2-107 • A3P015 Global Resource
 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.66	0.81	0.75	0.92	0.88	1.08	ns
t_{RCKH}	Input High Delay for Global Clock	0.67	0.84	0.76	0.96	0.89	1.13	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.18		0.21		0.25	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage-supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-108 • A3P030 Global Resource
 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.67	0.81	0.76	0.92	0.89	1.09	ns
t_{RCKH}	Input High Delay for Global Clock	0.68	0.85	0.77	0.97	0.91	1.14	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.18		0.21		0.24	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

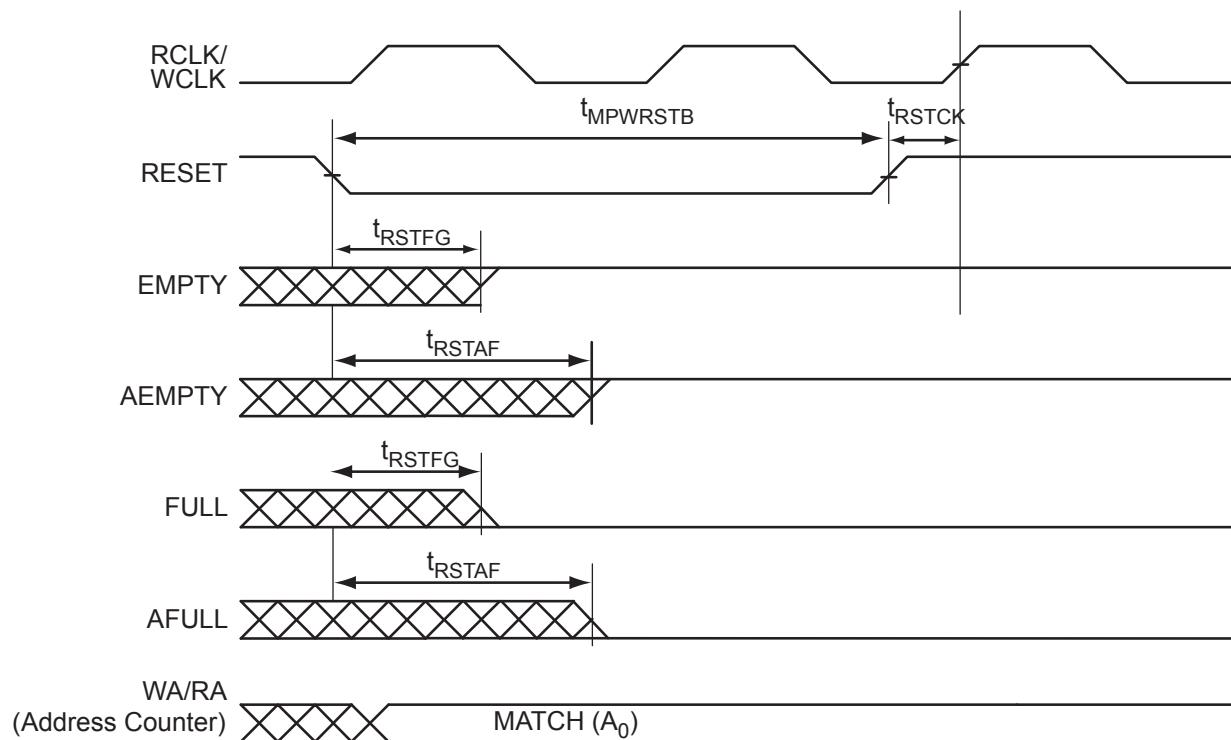


Figure 2-39 • FIFO Reset

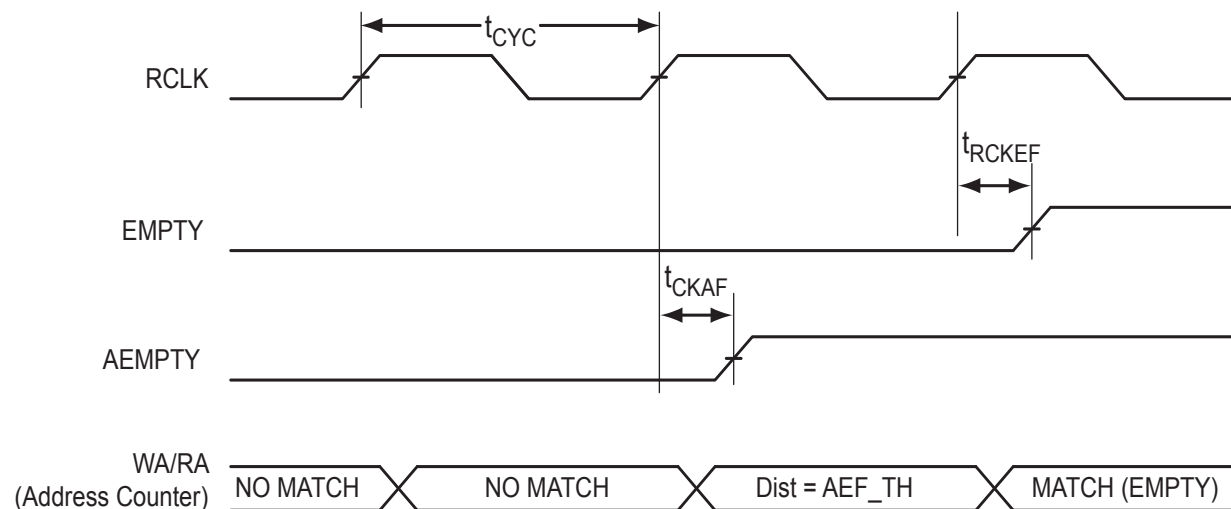


Figure 2-40 • FIFO EMPTY Flag and AEMPTY Flag Assertion

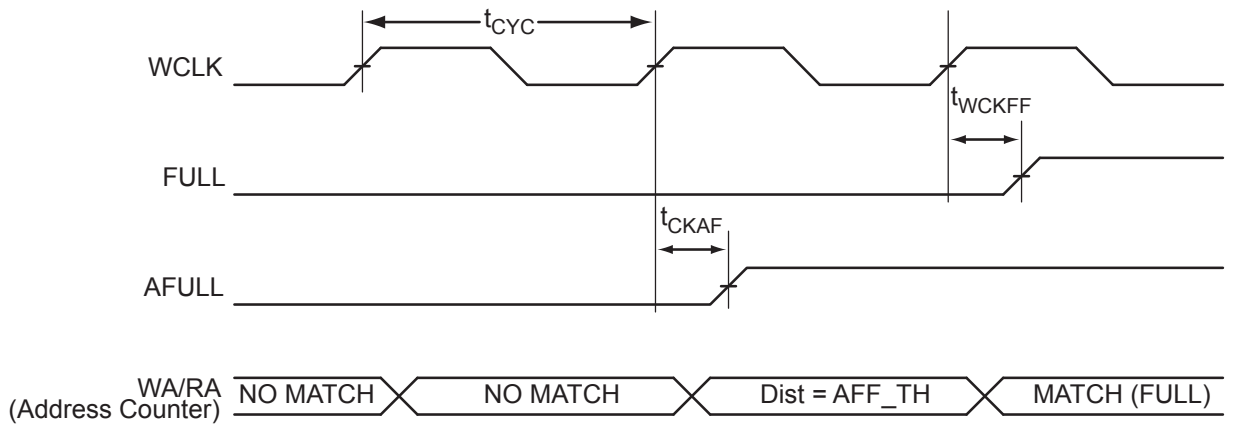


Figure 2-41 • FIFO FULL Flag and AFULL Flag Assertion

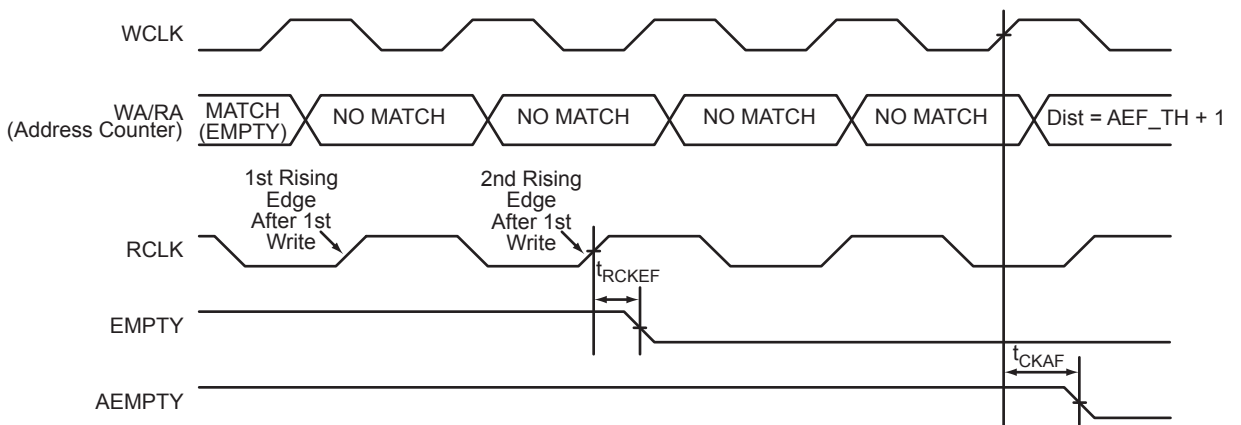


Figure 2-42 • FIFO EMPTY Flag and AEMPTY Flag Deassertion

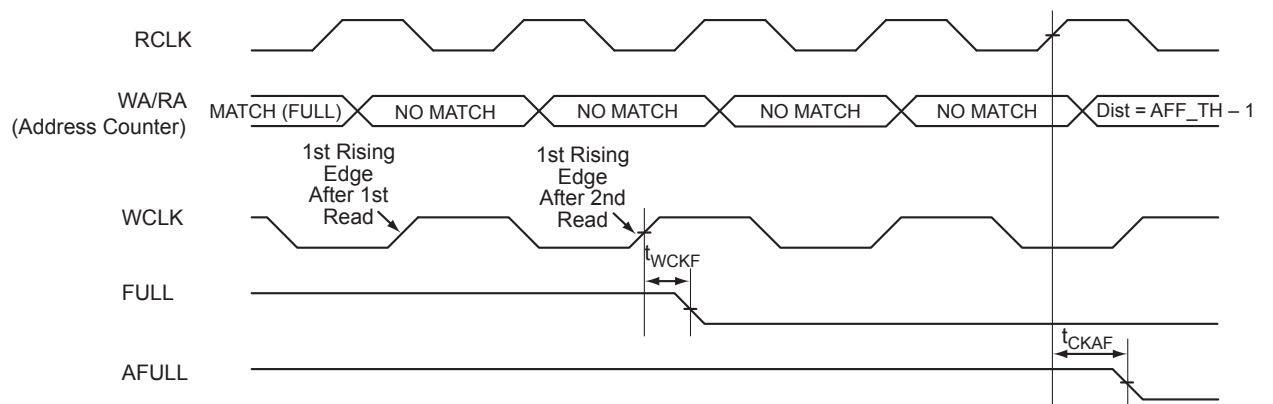


Figure 2-43 • FIFO FULL Flag and AFULL Flag Deassertion

QN132	
Pin Number	A3P250 Function
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

VQ100	
Pin Number	A3P125 Function
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1
36	IO93RSB1

VQ100	
Pin Number	A3P125 Function
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0
72	IO42RSB0

VQ100	
Pin Number	A3P125 Function
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

PQ208	
Pin Number	A3P250 Function
109	TRST
110	VJTAG
111	GDA0/IO60VDB1
112	GDA1/IO60UDB1
113	GDB0/IO59VDB1
114	GDB1/IO59UDB1
115	GDC0/IO58VDB1
116	GDC1/IO58UDB1
117	IO57VDB1
118	IO57UDB1
119	IO56NDB1
120	IO56PDB1
121	IO55RSB1
122	GND
123	VCCIB1
124	NC
125	NC
126	VCC
127	IO53NDB1
128	GCC2/IO53PDB1
129	GCB2/IO52PSB1
130	GND
131	GCA2/IO51PSB1
132	GCA1/IO50PDB1
133	GCA0/IO50NDB1
134	GCB0/IO49NDB1
135	GCB1/IO49PDB1
136	GCC0/IO48NDB1
137	GCC1/IO48PDB1
138	IO47NDB1
139	IO47PDB1
140	VCCIB1
141	GND
142	VCC
143	IO46RSB1
144	IO45NDB1

PQ208	
Pin Number	A3P250 Function
145	IO45PDB1
146	IO44NDB1
147	IO44PDB1
148	IO43NDB1
149	GBC2/IO43PDB1
150	IO42NDB1
151	GBB2/IO42PDB1
152	IO41NDB1
153	GBA2/IO41PDB1
154	VMV1
155	GNDQ
156	GND
157	NC
158	GBA1/IO40RSB0
159	GBA0/IO39RSB0
160	GBB1/IO38RSB0
161	GBB0/IO37RSB0
162	GND
163	GBC1/IO36RSB0
164	GBC0/IO35RSB0
165	IO34RSB0
166	IO33RSB0
167	IO32RSB0
168	IO31RSB0
169	IO30RSB0
170	VCCIB0
171	VCC
172	IO29RSB0
173	IO28RSB0
174	IO27RSB0
175	IO26RSB0
176	IO25RSB0
177	IO24RSB0
178	GND
179	IO23RSB0
180	IO22RSB0

PQ208	
Pin Number	A3P250 Function
181	IO21RSB0
182	IO20RSB0
183	IO19RSB0
184	IO18RSB0
185	IO17RSB0
186	VCCIB0
187	VCC
188	IO16RSB0
189	IO15RSB0
190	IO14RSB0
191	IO13RSB0
192	IO12RSB0
193	IO11RSB0
194	IO10RSB0
195	GND
196	IO09RSB0
197	IO08RSB0
198	IO07RSB0
199	IO06RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

FG256	
Pin Number	A3P250 Function
P9	IO76RSB2
P10	IO71RSB2
P11	IO66RSB2
P12	NC
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO60VDB1
R1	GEA1/IO98PDB3
R2	GEA0/IO98NDB3
R3	NC
R4	GEC2/IO95RSB2
R5	IO91RSB2
R6	IO88RSB2
R7	IO84RSB2
R8	IO80RSB2
R9	IO77RSB2
R10	IO72RSB2
R11	IO68RSB2
R12	IO65RSB2
R13	GDB2/IO62RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO94RSB2
T3	GEB2/IO96RSB2
T4	IO93RSB2
T5	IO90RSB2
T6	IO87RSB2
T7	IO83RSB2
T8	IO79RSB2
T9	IO78RSB2
T10	IO73RSB2
T11	IO70RSB2
T12	GDC2/IO63RSB2

FG256	
Pin Number	A3P250 Function
T13	IO67RSB2
T14	GDA2/IO61RSB2
T15	TMS
T16	GND

FG256	
Pin Number	A3P400 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO16RSB0
A6	IO17RSB0
A7	IO22RSB0
A8	IO28RSB0
A9	IO34RSB0
A10	IO37RSB0
A11	IO41RSB0
A12	IO43RSB0
A13	GBB1/IO57RSB0
A14	GBA0/IO58RSB0
A15	GBA1/IO59RSB0
A16	GND
B1	GAB2/IO154UDB3
B2	GAA2/IO155UDB3
B3	IO12RSB0
B4	GAB1/IO03RSB0
B5	IO13RSB0
B6	IO14RSB0
B7	IO21RSB0
B8	IO27RSB0
B9	IO32RSB0
B10	IO38RSB0
B11	IO42RSB0
B12	GBC1/IO55RSB0
B13	GBB0/IO56RSB0
B14	IO44RSB0
B15	GBA2/IO60PDB1
B16	IO60NDB1
C1	IO154VDB3
C2	IO155VDB3
C3	IO11RSB0
C4	IO07RSB0

FG256	
Pin Number	A3P400 Function
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0
C7	IO20RSB0
C8	IO24RSB0
C9	IO33RSB0
C10	IO39RSB0
C11	IO45RSB0
C12	GBC0/IO54RSB0
C13	IO48RSB0
C14	VMV0
C15	IO61NPB1
C16	IO63PDB1
D1	IO151VDB3
D2	IO151UDB3
D3	GAC2/IO153UDB3
D4	IO06RSB0
D5	GNDQ
D6	IO10RSB0
D7	IO19RSB0
D8	IO26RSB0
D9	IO30RSB0
D10	IO40RSB0
D11	IO46RSB0
D12	GNDQ
D13	IO47RSB0
D14	GBB2/IO61PPB1
D15	IO53RSB0
D16	IO63NDB1
E1	IO150PDB3
E2	IO08RSB0
E3	IO153VDB3
E4	IO152VDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO25RSB0

FG256	
Pin Number	A3P400 Function
E9	IO31RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1
E13	GBC2/IO62PDB1
E14	IO65RSB1
E15	IO52RSB0
E16	IO66PDB1
F1	IO150NDB3
F2	IO149NPB3
F3	IO09RSB0
F4	IO152UDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO62NDB1
F14	IO49RSB0
F15	IO64PPB1
F16	IO66NDB1
G1	IO148NDB3
G2	IO148PDB3
G3	IO149PPB3
G4	GFC1/IO147PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1

Revision	Changes	Page
v2.0 (continued)	Table 3-20 • Summary of I/O Timing Characteristics—Software Default Settings (Advanced) and Table 3-21 • Summary of I/O Timing Characteristics—Software Default Settings (Standard Plus) were updated.	3-20 to 3-20
	Table 3-11 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices was updated.	3-9
	Table 3-24 • I/O Output Buffer Maximum Resistances ¹ (Advanced) and Table 3-25 • I/O Output Buffer Maximum Resistances ¹ (Standard Plus) were updated.	3-22 to 3-22
	Table 3-17 • Summary of Maximum and Minimum DC Input Levels Applicable to Commercial and Industrial Conditions was updated.	3-18
	Table 3-28 • I/O Short Currents IOSH/IOSL (Advanced) and Table 3-29 • I/O Short Currents IOSH/IOSL (Standard Plus) were updated.	3-24 to 3-26
	The note in Table 3-32 • I/O Input Rise Time, Fall Time, and Related I/O Reliability was updated.	3-27
	Figure 3-33 • Write Access After Write onto Same Address, Figure 3-34 • Read Access After Write onto Same Address, and Figure 3-35 • Write Access After Read onto Same Address are new.	3-82 to 3-84
	Figure 3-43 • Timing Diagram was updated.	3-96
	Ambient was deleted from the "Speed Grade and Temperature Grade Matrix".	iv
	Notes were added to the package diagrams identifying if they were top or bottom view.	N/A
	The A3P030 "132-Pin QFN" table is new.	4-2
	The A3P060 "132-Pin QFN" table is new.	4-4
	The A3P125 "132-Pin QFN" table is new.	4-6
	The A3P250 "132-Pin QFN" table is new.	4-8
	The A3P030 "100-Pin VQFP" table is new.	4-11
Advance v0.7 (January 2007)	In the "I/Os Per Package" table, the I/O numbers were added for A3P060, A3P125, and A3P250. The A3P030-VQ100 I/O was changed from 79 to 77.	ii
Advance v0.6 (April 2006)	The term flow-through was changed to pass-through.	N/A
	Table 1 was updated to include the QN132.	ii
	The "I/Os Per Package" table was updated with the QN132. The footnotes were also updated. The A3P400-FG144 I/O count was updated.	ii
	"Automotive ProASIC3 Ordering Information" was updated with the QN132.	iii
	"Temperature Grade Offerings" was updated with the QN132.	iii
	B-LVDS and M-LDVS are new I/O standards added to the datasheet.	N/A
	The term flow-through was changed to pass-through.	N/A
	Figure 2-7 • Efficient Long-Line Resources was updated.	2-7
	The footnotes in Figure 2-15 • Clock Input Sources Including CLKBUF, CLKBUF_LVDS/LVPECL, and CLKINT were updated.	2-16
	The Delay Increments in the Programmable Delay Blocks specification in Figure 2-24 • ProASIC3E CCC Options.	2-24
	The "SRAM and FIFO" section was updated.	2-21